



**DMMT3904W** 

#### **40V MATCHED PAIR NPN SMALL SIGNAL TRANSISTOR IN SOT363**

#### **Features**

- BVceo > 40V
- I<sub>C</sub> = 200mA high Collector Current
- Pair of NPN transistors that are intrinsically matched (Note 1)
- 2% Matching on Current Gain (h<sub>FE</sub>)
- 2mV Matching on Base-Emitter Voltage (V<sub>BE</sub>)
- Fully internally isolated in a small surface mount package
- Totally Lead-Free & Fully RoHS Compliant (Notes 2 & 3)
- Halogen and Antimony Free. "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 5)

#### **Mechanical Data**

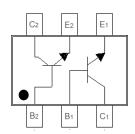
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.006 grams (approximate)

#### **Applications**

- Current mirrors
- Differential and instrumentation amplifiers
- Comparators



Top View



Device Schematic and Pin-Out Top View

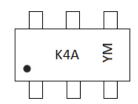
#### Ordering Information (Note 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMMT3904W-7-F	AEC-Q101	K4A	7	8	3,000
DMMT3904WQ-7-F	Automotive	K4A	7	8	3,000

Notes:

- 1. Intrinsically matched pair as this is built with adjacent die from the same wafer.
- 2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 3. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product compliance definitions/.
- 6. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K4A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 2 = February)

Date Code Key

Year	2010	201	11	2012	20	013	2014	2	2015	2016		2017
Code	Х	Y		Z		Α	В		С	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	200	mA

## Thermal Characteristics – Total Device (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7) Total Device	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Note:

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

#### Thermal Characteristics – Total Device

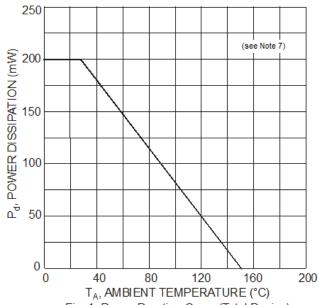


Fig. 1, Power Derating Curve (Total Device)

<sup>7.</sup> For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.



## Electrical Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage(Note 9)	BV <sub>CEO</sub>	40	_	_	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	_	_	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	_	_	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
Base Cutoff Current	I <sub>BL</sub>	_	_	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
ON CHARACTERISTICS (Note 9)						
DC Current Gain	hFE	40 70 100 60 30	_	300 — —	_	$I_{C} = 100 \mu A, V_{CE} = 1.0 V$ $I_{C} = 1.0 m A, V_{CE} = 1.0 V$ $I_{C} = 10 m A, V_{CE} = 1.0 V$ $I_{C} = 50 m A, V_{CE} = 1.0 V$ $I_{C} = 100 m A, V_{CE} = 1.0 V$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	200 300	mV	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	_	850 950	mV	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
MATCHING CHARACTERISTICS						
DC Current Gain Matching (Note 10)	h <sub>FE1</sub> / h <sub>FE2</sub>	_	1	2	%	$I_C$ = 2mA, $V_{CE}$ = 5V
Base-Emitter Voltage Matching (Note 11)	V <sub>BE1</sub> - V <sub>BE2</sub>	_	1	2	mV	$I_C$ = 2mA, $V_{CE}$ = 5V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(SAT)1</sub> / V <sub>CE(SAT)2</sub>	_	1	2	%	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(SAT)1</sub> / V <sub>BE(SAT)2</sub>	_	1	2	%	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	_	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	_	8	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0 \text{mA},$
Small Signal Current Gain	h <sub>fe</sub>	100	_	400	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	_	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	_	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	_	_	5.0	dB	$V_{CE} = 5.0V$ , $I_{C} = 100\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$
SWITCHING CHARACTERISTICS	•		•	•	·	
Delay Time	t <sub>d</sub>	_	_	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Rise Time	t <sub>r</sub>	_	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	_	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Fall Time	t <sub>f</sub>	_	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

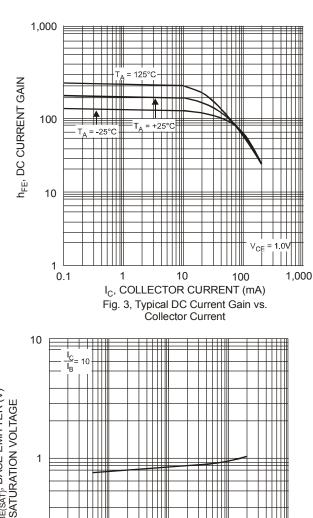
Note:

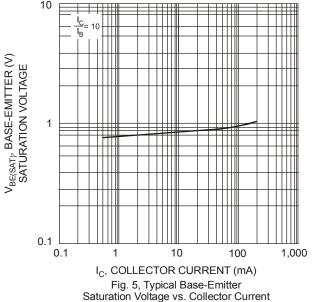
<sup>9.</sup> Measured under pulsed conditions. Pulse width  $\le$  300 $\mu$ s. Duty cycle  $\le$  2%. 10. Is the ratio of one transistor compared to the other transistor.

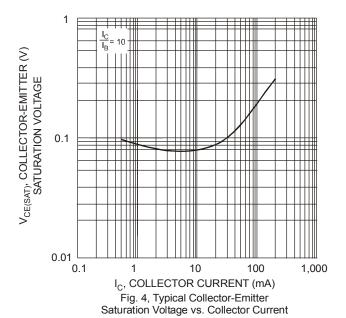
<sup>11.</sup>  $V_{\text{BE1}}$  -  $V_{\text{BE2}}$  is the absolute difference of one transistor compared to the other transistor.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)





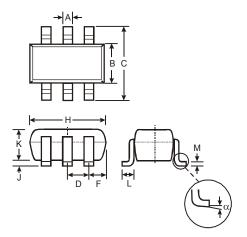


15 f = 1MHz  $C_{\rm BO},$  INPUT CAPACITANCE (pF)  $C_{\rm OBO},$  OUTPUT CAPACITANCE (pF) 10 5 0 0.1 10  $V_{CB}$ , COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



## **Package Outline Dimensions**

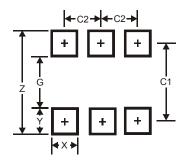
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT363					
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
C	2.00	2.20	2.10			
D	0.65 Typ					
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
M	0.10	0.22	0.11			
α	0°	8°	-			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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